

MITSUBISHI HIGH SPEED CMOS M74HC280P/FP/DP

9-BIT ODD/EVEN PARITY GENERATOR/CHECKER

DESCRIPTION

The M74HC280 is a semiconductor integrated circuit consisting of a 9-bit parity generator/checker.

FEATURES

- High-speed: 20ns typ. ($C_L=15\text{pF}$, $V_{CC}=5\text{V}$)
- Low power dissipation: $20\mu\text{W}/\text{package}$, max ($V_{CC}=5\text{V}$, $T_a=25^\circ\text{C}$, quiescent state)
- High noise margin: 30% of V_{CC} , min ($V_{CC}=4.5\text{V}$, 6V)
- Capable of driving 10 74LSTTL loads
- Wide supply voltage range: $V_{CC}=2\sim 6\text{V}$
- Wide operating temperature range: $T_a=-40\sim +85^\circ\text{C}$

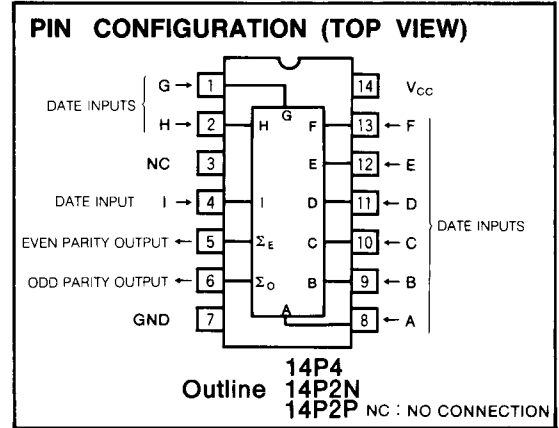
APPLICATION

General purpose, for use in industrial and consumer digital equipment.

FUNCTIONAL DESCRIPTION

Use of silicon gate technology allows the M74HC280 to maintain the low power dissipation and high noise margin characteristics of the standard CMOS logic 4000B series while giving high-speed performance equivalent to the 74LS280.

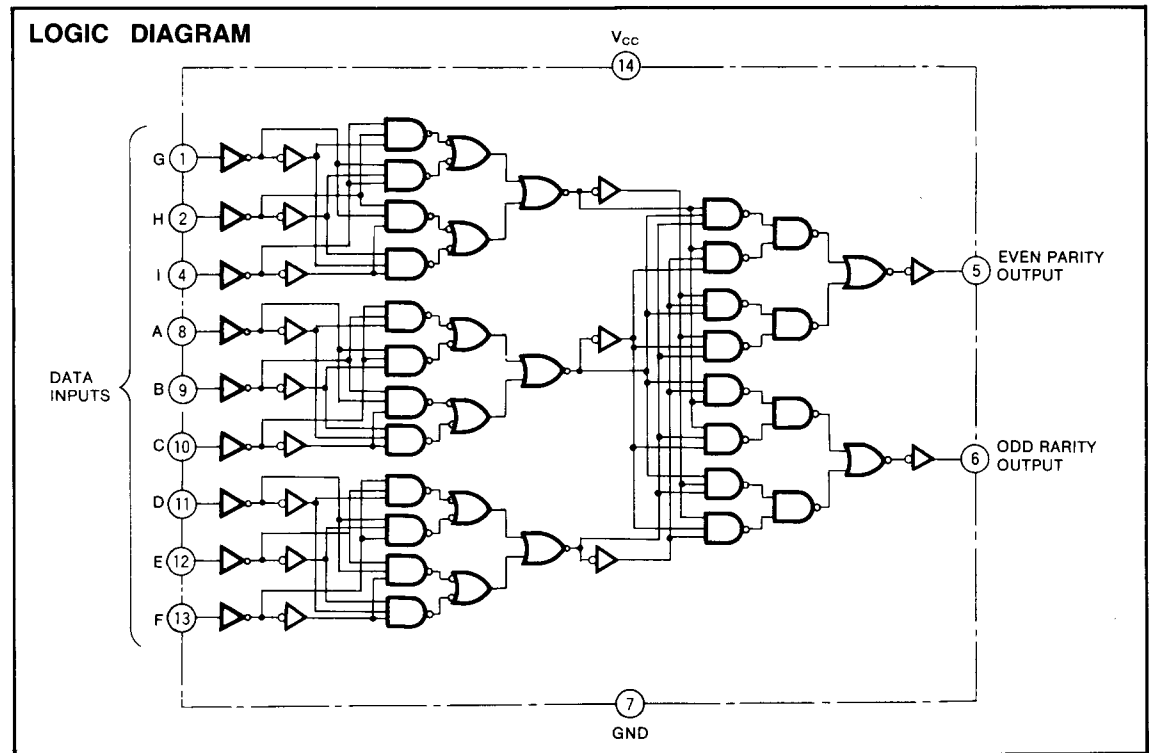
The M74HC280 combines the functions of a 9-bit parity generator and a parity checker. When used as a parity generator, applying 9-bit data to date inputs A through I will result in a generation of parity output to the even parity output or the odd parity output depending upon the number of



high values in the data input. See the Function Table for details. When used as a parity checker, one bit from among the 9 bits of data input is used as an odd or even parity designation and the remaining eight bits are used as date.

FUNCTION TABLE

Number of date input high values	EVEN PARITY	ODD PARITY
Even	H	L
Odd	L	H



9-BIT ODD/EVEN PARITY GENERATOR/CHECKER

ABSOLUTE MAXIMUM RATINGS ($T_a = -40 \sim +85^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CC}	Supply voltage		$-0.5 \sim +7.0$	V
V_I	Input voltage		$-0.5 \sim V_{CC} + 0.5$	V
V_O	Output voltage		$-0.5 \sim V_{CC} + 0.5$	V
I_{IK}	Input protection diode current	$V_I < 0V$	-20	mA
		$V_I > V_{CC}$	20	
I_{OK}	Output parasitic diode current	$V_O < 0V$	-20	mA
		$V_O > V_{CC}$	20	
I_O	Output current per output pin		± 25	mA
I_{CC}	Supply/GND current	V_{CC}, GND	± 50	mA
P_d	Power dissipation	(Note 1)	500	mW
T_{stg}	Storage temperature range		$-65 \sim +150$	$^\circ\text{C}$

Note 1 : M74HC280FP, $T_a = -40 \sim +60^\circ\text{C}$ and $T_a = 60 \sim 85^\circ\text{C}$ are derated at $-6\text{mW}/^\circ\text{C}$.
M74HC280DP, $T_a = -40 \sim +50^\circ\text{C}$ and $T_a = 50 \sim 85^\circ\text{C}$ are derated at $-5\text{mW}/^\circ\text{C}$.

RECOMMENDED OPERATING CONDITIONS ($T_a = -40 \sim +85^\circ\text{C}$)

Symbol	Parameter	Limits			Unit
		Min	Typ	Max	
V_{CC}	Supply voltage	2		6	V
V_I	Input voltage	0		V_{CC}	V
V_O	Output voltage	0		V_{CC}	V
T_{opr}	Operating temperature range	-40		$+85$	$^\circ\text{C}$
t_r, t_f	Input risetime, falltime	$V_{CC} = 2.0V$	0	1000	ns
		$V_{CC} = 4.5V$	0	500	
		$V_{CC} = 6.0V$	0	400	

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits					Unit
			25 $^\circ\text{C}$			$-40 \sim +85^\circ\text{C}$		
			$V_{CC}(V)$	Min	Typ	Max	Min	
V_{IH}	High-level input voltage	$V_O = 0.1V, V_{CC} = 0.1V$ $ I_O = 20\mu A$	2.0	1.5			1.5	V
			4.5	3.15			3.15	
			6.0	4.2			4.2	
V_{IL}	Low-level input voltage	$V_O = 0.1V, V_{CC} = 0.1V$ $ I_O = 20\mu A$	2.0			0.5	0.5	V
			4.5			1.35	1.35	
			6.0			1.8	1.8	
V_{OH}	High-level output voltage	$V_I = V_{IH}, V_{IL}$	$I_{OH} = -20\mu A$	2.0	1.9		1.9	V
			$I_{OH} = -20\mu A$	4.5	4.4		4.4	
			$I_{OH} = -20\mu A$	6.0	5.9		5.9	
			$I_{OH} = -4.0mA$	4.5	4.18		4.13	
			$I_{OH} = -5.2mA$	6.0	5.68		5.63	
V_{OL}	Low-level output voltage	$V_I = V_{IH}, V_{IL}$	$I_{OL} = 20\mu A$	2.0		0.1	0.1	V
			$I_{OL} = 20\mu A$	4.5		0.1	0.1	
			$I_{OL} = 20\mu A$	6.0		0.1	0.1	
			$I_{OL} = 4.0mA$	4.5		0.26	0.33	
			$I_{OL} = 5.2mA$	6.0		0.26	0.33	
I_{IH}	High-level input current	$V_I = 6V$	6.0			0.1	1.0	μA
I_{IL}	Low-level input current	$V_I = 0V$	6.0			-0.1	-1.0	μA
I_{CC}	Quiescent supply current	$V_I = V_{CC}, GND, I_O = 0\mu A$	6.0			4.0	40.0	μA

9-BIT ODD/EVEN PARITY GENERATOR/CHECKER

SWITCHING CHARACTERISTICS (V_{CC} = 5V, T_a = 25°C)

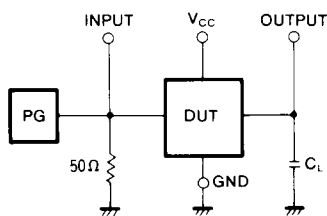
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
t _{TLH}	Low-level to high-level and high-level to low-level output transition time	C _L = 15pF (Note 3)			10	ns
t _{THL}					10	ns
t _{PLH}	Low-level to high-level and high-level to low-level output propagation time				35	ns
t _{PHL}					35	ns

SWITCHING CHARACTERISTICS (V_{CC} = 2~6V, T_a = -40~+85°C)

Symbol	Parameter	Test conditions	Limits						Unit
			25°C			-40~+85°C			
			V _{CC} (V)	Min	Typ	Max	Min	Max	
t _{TLH}	Low-level to high-level and high-level to low-level output transition time	C _L = 50pF (Note 3)	2.0			75		95	ns
			4.5			15		19	
			6.0			13		16	
t _{THL}	output transition time		2.0			75		95	ns
			4.5			15		19	
			6.0			13		16	
t _{PLH}	Low-level to high-level and high-level to low-level output propagation time		2.0			205		258	ns
			4.5			41		52	
			6.0			35		44	
t _{PHL}	A~I EVEN PARITY ODD PARITY	2.0			205		258	ns	
		4.5			41		52		
		6.0			35		44		
C _I	Input capacitance				10		10	pF	
C _{PD}	Power dissipation capacitance (Note 2)			92				pF	

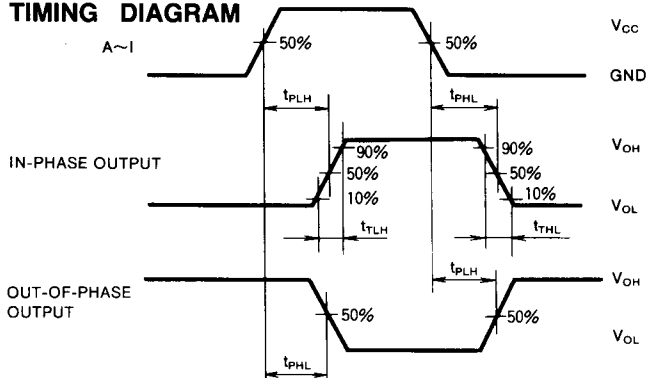
Note 2 : C_{PD} is the internal capacitance of the IC calculated from operation supply current under no-load conditions. (per gate)
 The power dissipated during operation under no-load conditions is calculated using the following formula:
 $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_i + I_{CC} \cdot V_{CC}$

Note 3 : Test Circuit



- (1) The pulse generator (PG) has the following characteristics (10%~90%): t_r = 6ns, t_f = 6ns
- (2) The capacitance C_L includes stray wiring capacitance and the probe input capacitance.

TIMING DIAGRAM



**MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES**

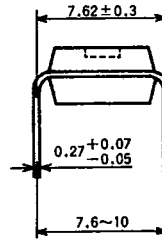
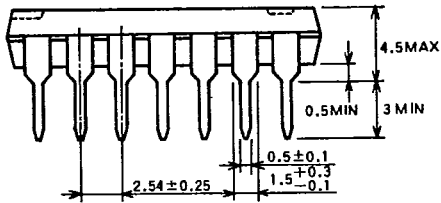
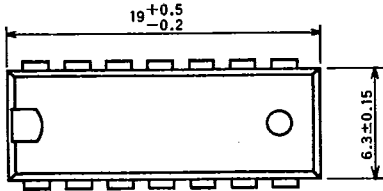
6249827 MITSUBISHI (DGTL LOGIC)

91D 12849

D T-90-20

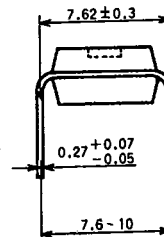
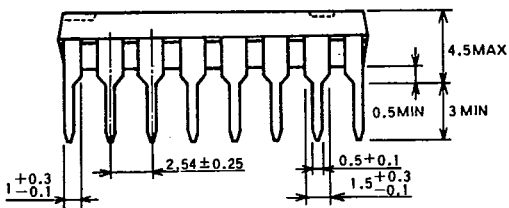
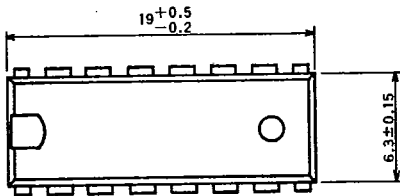
TYPE 14P4 14-PIN MOLDED PLASTIC DIP

Dimension in mm



TYPE 16P4 16-PIN MOLDED PLASTIC DIP

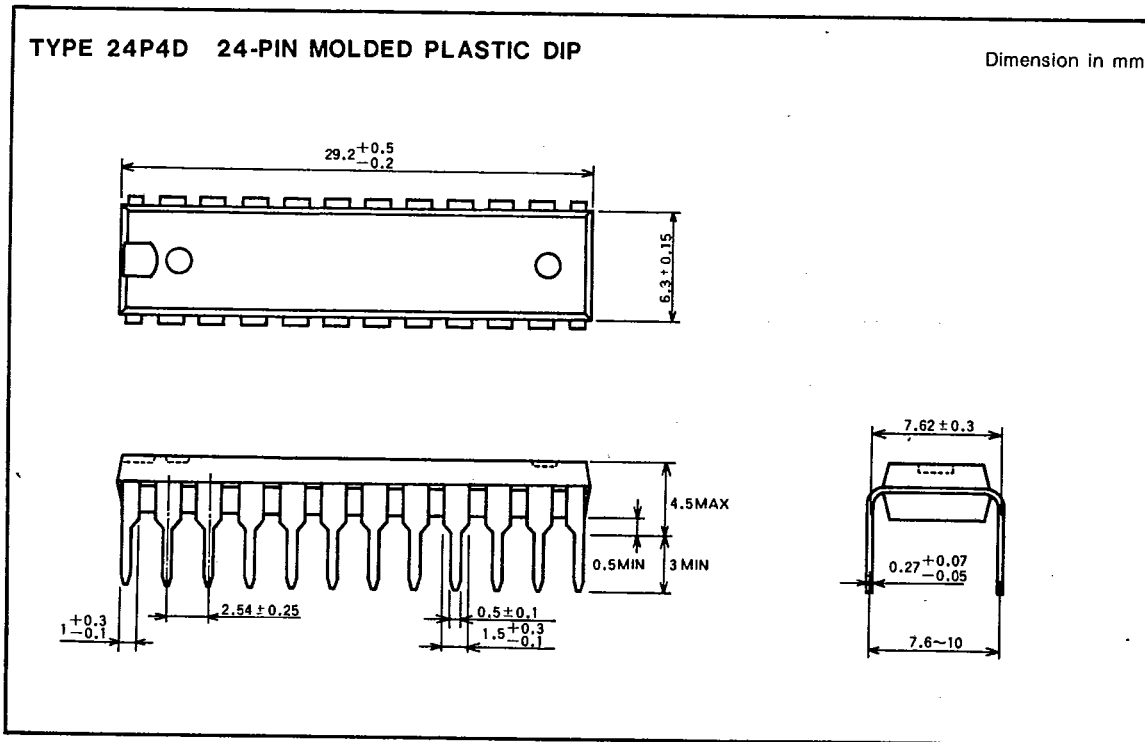
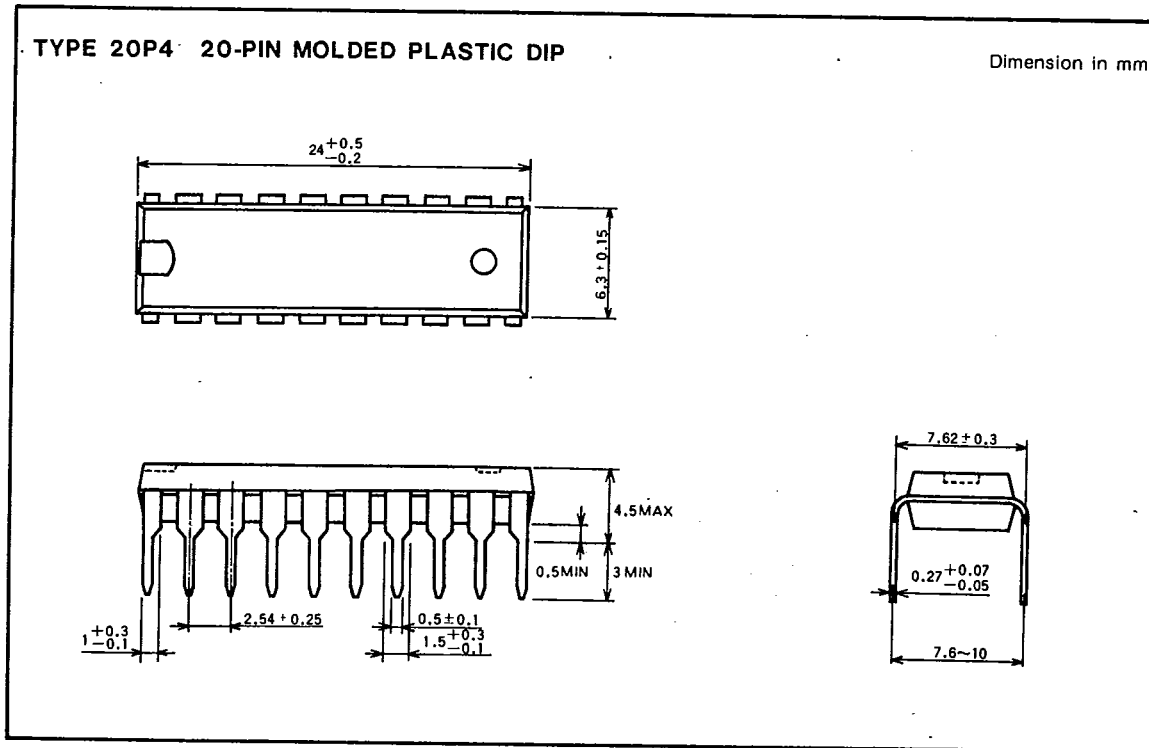
Dimension in mm



MITSUBISHI HIGH SPEED CMOS
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91D 12850 D.T-90-20



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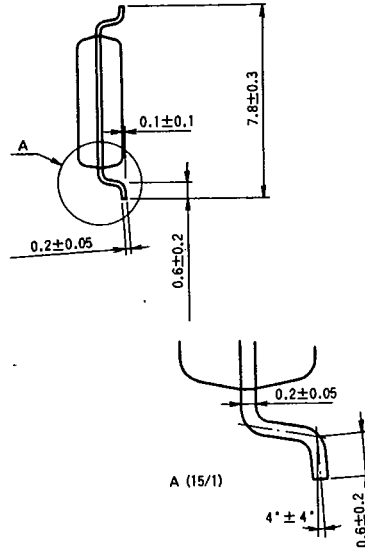
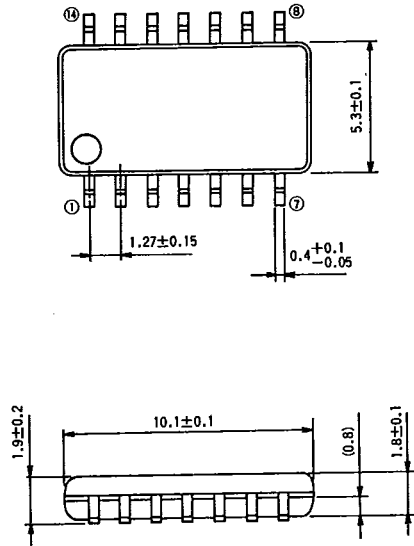
MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES

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91D 12851 D T-90.20

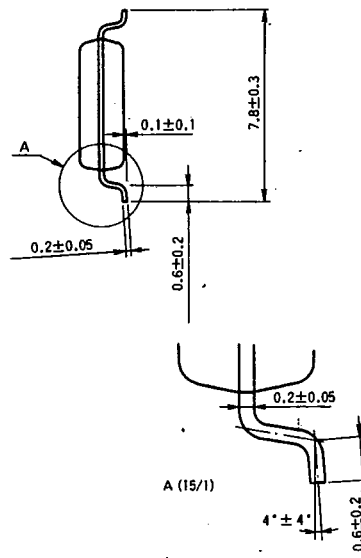
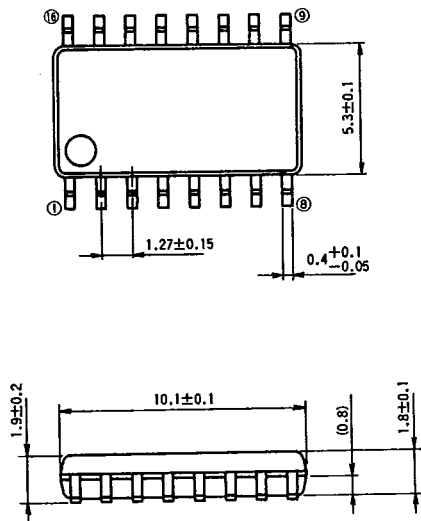
TYPE 14P2N 14PIN MOLDED PLASTIC SOP

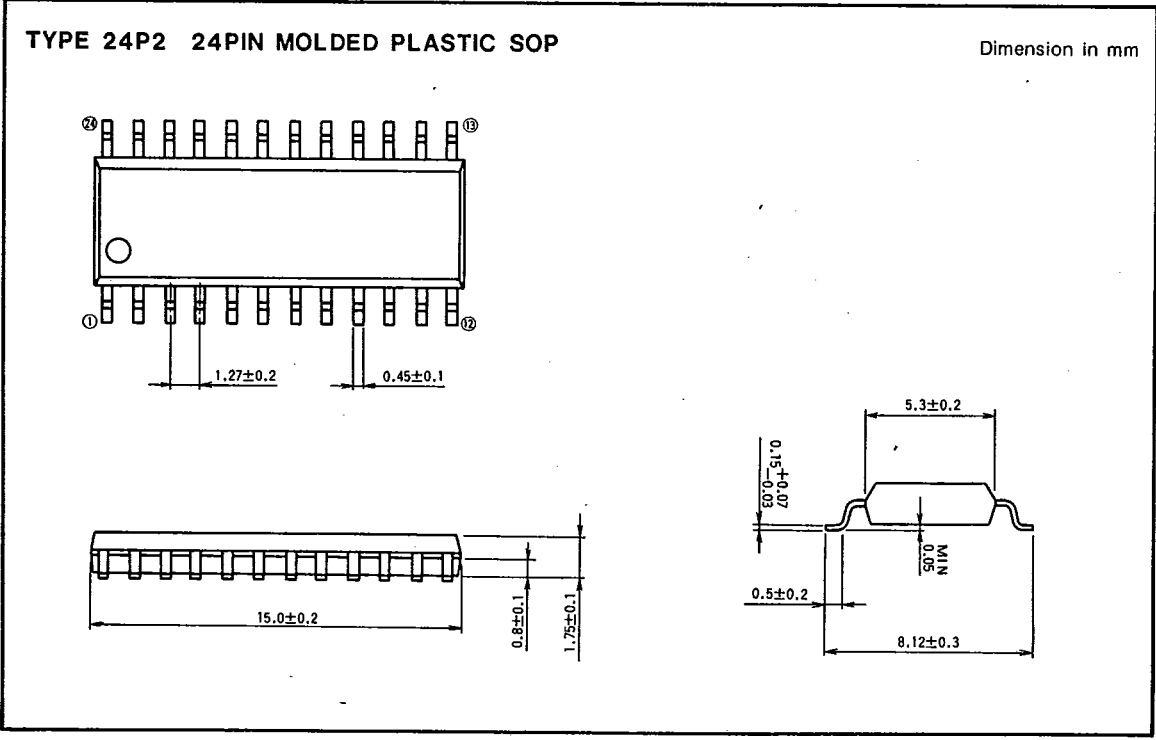
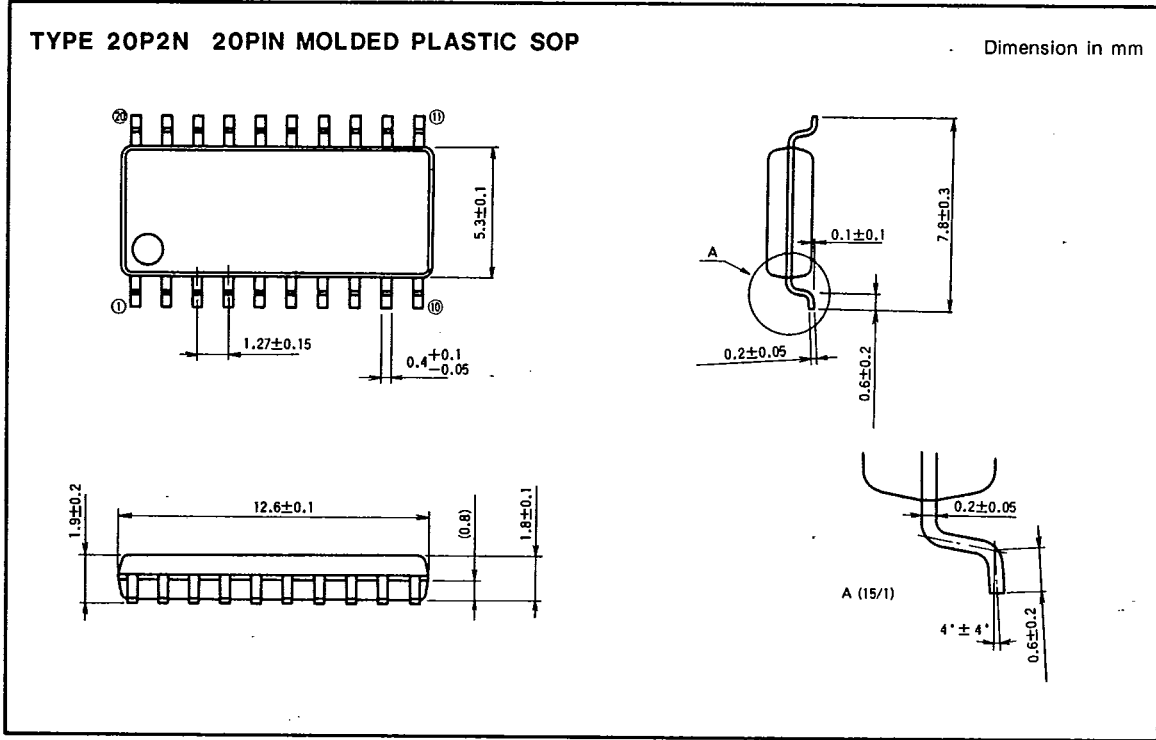
Dimension in mm

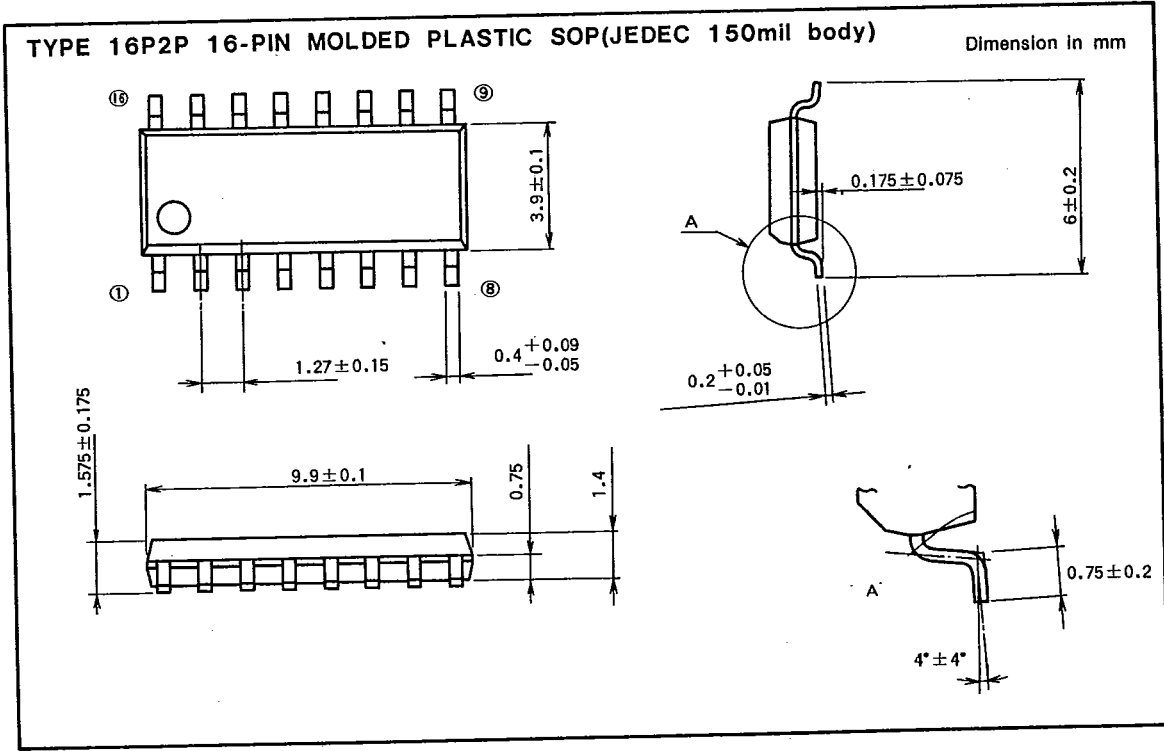
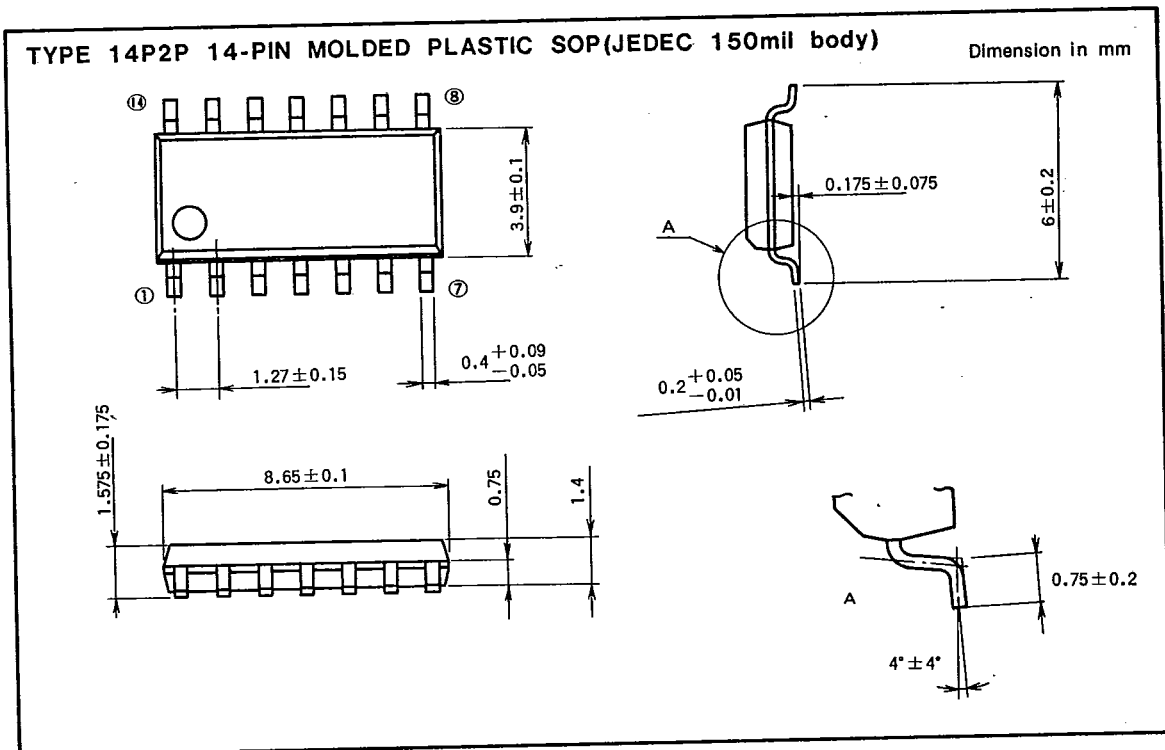


TYPE 16P2N 16PIN MOLDED PLASTIC SOP

Dimension in mm







MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES

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91D 12854 D T-90-20

